F4280 Technologie depozice tenkých vrstev a povrchových úprav 2. Gas Kinetics

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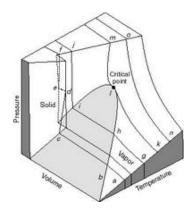


Outline - chapter 2. Gas Kinetics

- 2.1 Vapors and Gases
- 2.2 Maxwell-Boltzmann Distribution
- 2.3 Ideal-Gas Law
- 2.4 Molecular Impingement Flux
- 2.5 Units of Measurement
- 2.6 Knudsen Equation
- 2.7 Mean Free Path
- 2.8 Transport Properties

p-V-T diagram

The possible equilibrium states can be represented in pressure-volume-temperature (p-V-T) space for fixed amount of material (e.g. 1 mol = 6.02×10^{23}):



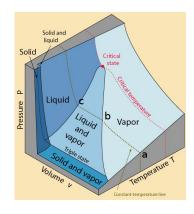
A cut through the p-V-T surface below critical point for fixed $T \Rightarrow$ relationship between p and $V_{\rm m}$ (molar volume)

- ▶ point a: highest V (lowest p) vapor phase
- ▶ from point a to b: reducing $V \rightarrow$ increasing p
- point b: condensation begins
- From point b to c: V is decreasing at fixed p and T (b − c line is ⊥ to the p-T plane, p is called saturation vapor pressure p_v or just vapor pressure)
- ▶ point c: condensation completed

If *V* is abruptly decreased in b-c transition *p* would be pushed above the line $b-c \Rightarrow$ non-equilibrium supersaturated vapors

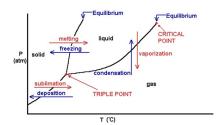
p-V-T diagram

It is important to distinguish between the behaviors of vapors and gases:

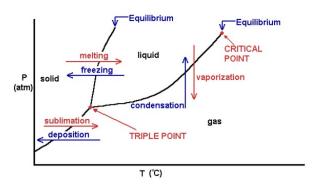


- vapors: can be condensed to liquid or solid by compression at fixed $T \Rightarrow$ below critical point defined by p_c , V_c and T_c
- gases: monotonical decrease of V upon compression ⇒ no distinction between the two phases

Surfaces "liquid-vapor", "solid-vapor" and "solid-liquid" are perpendicular to the p-T plane ⇒ their projection on that plane are lines.



p-T diagram



- ▶ triple point: from triple line ⊥ to p-T plane
- ▶ below T of triple point: liquid-phase region vanishes ⇒ condensation directly to the solid phase, vaporization in this region is sublimation
- pressure along borders of vapor region is vapor pressure p_v
- $p_{\rm v}$ increases exponentially with T up to $p_{\rm c}$ that is well above 1 atm \Rightarrow deposition of thin films is performed at $p \ll p_{\rm c}$, either $p > p_{\rm v}$ (supersaturated vapors) or $p < p_{\rm v}$

Maxwell-Boltzmann Distribution

Distribution of random velocities \vec{V} in equilibrium state

$$f(\vec{V}) = n \left(\frac{m}{2\pi k_{\rm B}T}\right)^{3/2} \exp\left(-\frac{mV^2}{2k_{\rm B}T}\right)$$
 (1)

where $k_{\rm B}=1.38\times 10^{-23}$ m² kg s⁻² K⁻¹ (or J K⁻¹) is the Boltzmann constant, n, T and m are particle density, temperature and mass, respectively.

If the drift velocity is zero we do not need to distinguish between the velocity and random velocity, i.e. $\vec{v} \equiv \vec{V}$.

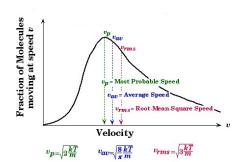
Maxwell-Boltzmann distribution is isotropic $\Rightarrow F(v)$ distribution of speeds $v \equiv |\vec{v}|$ can be defined by integration of f(v) in spherical coordinates

$$F(v)dv = \int_0^\pi \int_0^{2\pi} f(v)v^2 \sin\theta d\phi d\theta dv$$
 (2)

resulting in

$$F(v) = 4\pi v^2 n \left(\frac{m}{2\pi k_{\rm B}T}\right)^{3/2} \exp\left(-\frac{mv^2}{k_{\rm B}T}\right)$$
(3)

Mean (Average) Speed, Molecular Impingement Flux



Root-mean-square (rms) speed:

$$v_{\rm rms} = \frac{1}{n} \int_{0}^{\infty} F(v) v^2 dv = \sqrt{\frac{3k_{\rm B}T}{\pi m}}$$
 (6)

Mean speed:

$$\langle v \rangle = v_{\rm av} = \frac{1}{n} \int_0^\infty F(v) v dv = \sqrt{\frac{8k_{\rm B}T}{\pi m}} (4)$$

or

$$v_{\rm av} = \sqrt{\frac{8RT}{M}} \tag{5}$$

using molar mass $\textit{M} = \textit{mN}_{A}$ in kg/mol and gas constant

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$$R = k_{\rm B}N_{\rm A} = 8.31~{
m Jmol}^{-1}{
m K}^{-1}$$

re $N_{\rm A} = 6.02 \times 10^{23}~{
m mol}^{-1}$ is

where $N_{\rm A}=6.02\times 10^{23}~{\rm mol^{-1}}$ is Avogadro's number

The most probable speed v_p :

$$\left(\frac{dF(v)}{dv}\right)_{v=v_{\rm D}} = 0 \Rightarrow v_{\rm p} = \sqrt{\frac{2k_{\rm B}T}{m}}$$
 (7)

Ideal-Gas Law

From the definition of pressure for ideal gas (not necessary to consider pressure tensor but only scalar pressure)

$$\rho = \frac{1}{3} mn \langle \vec{V}_x^2 + V_y^2 + V_z^2 \rangle = \frac{1}{3} mn \langle \vec{V}^2 \rangle = m \int_V V^2 f(V) d^3 V.$$
 (8)

The ideal-gas law is obtained by integration of (8) using Maxwell-Boltzmann distribution:

$$p = nk_{\rm B}T$$
 or $\frac{pV}{T} = Nk_{\rm B}$ (9)

where *N* is the number of particles.

Chemists are used to work in molar amounts:

- ▶ molar concentration $n_{\rm m} = n/N_{\rm A} \Rightarrow p = n_{\rm m}RT$
- ▶ number of moles $N_{\rm m} = N/N_{\rm A} \Rightarrow p = N_{\rm m}RT/V$
- ightharpoonup molar volume $V_{
 m m}=V/N_{
 m A} \Rightarrow p=RT/V_{
 m m}$

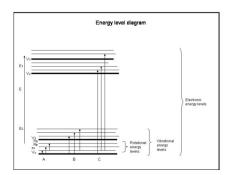
The ideal gas is obeyed if

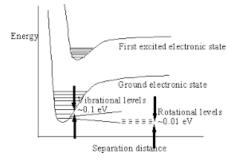
- ▶ the volume of molecules in the gas is much smaller than the volume of the gas
- the cohesive forces between the molecules can be neglected.

Both assumptions are fulfilled for low $n \Rightarrow$ always fulfilled for thin film deposition from the vapor phase ($T > T_{\rm room}$ and $p \le p_{\rm atm}$), i.e. well away from the critical point (most materials $p_c \gg 1$ atm or if not $T_c \ll 25\,^{\circ}{\rm C}$

Molecules can store energy in various forms. Their energetic states are quantized (spacing between energy levels ΔE)

- ightharpoonup electronic excitations $\Delta E_{\rm e}$ is highest, transitions between different electronic states are possible only for extremely high T or collision with energetic particle
- \blacktriangleright vibrational excitations energy levels correspond to different vibration modes of the molecule, $\Delta E_{\rm v}\approx$ 0.1 eV (1 eV = 11 600 K)
- lacktriangledown rotational excitations different rotational modes of the molecule, $\Delta E_{
 m r} pprox 0.01$ eV
- ranslational energy above performed description of molecular random motion $E_{\rm t}=1/2mV^2$, no details of inner molecule structure are considered, $\Delta E_{\rm t}$ negligible at ordinary T.





Energy Content of Gas

From definition of absolute temperature - the mean thermal energy kT/2 belongs to each translational degree of freedom and molecular translation energy is

$$E_{\rm t} = \frac{3}{2} k_{\rm B} T \tag{10}$$

 \Rightarrow equipartition theorem of classical statistical mechanics. Classical statistical treatment assumes very close quantized energy levels of molecules, i.e. approximated as a continuum. It is a good assumption for translational energy when $T \gg 0$ K.

- ► For **atomic** gases, *E*_t is total kinetic energy content.
- ▶ For molecular gases, E_r is added at ordinary T and E_v at very high T:

Molar heat capacity at constant volume $c_{\rm V}$ (for molecular gas) [J/(mol.K)] - increase of total kinetic energy for increasing T:

$$\frac{c_{\rm V}}{N_{\rm A}} = \frac{\mathrm{d}E_{\rm m}}{\mathrm{d}T} = \frac{\mathrm{d}(E_{\rm t} + E_{\rm r} + E_{\rm v})}{\mathrm{d}T} \tag{11}$$

for atomic gases

for small diatomic molecules at room *T*

$$c_{\mathrm{V}} = \frac{3}{2}R = \frac{3}{2}kN_{\mathrm{A}} \qquad \qquad c_{\mathrm{V}} = \frac{5}{2}R$$

- two rotational degrees of freedom are excited but vibrational ones are not

Energy Content of Gas

The heat capacity of any gas is larger when measured at constant pressure $c_{\rm p}$ - heat input is doing $p{\rm d}V$ work on the surroundings in addition to adding kinetic energy to the molecules:

$$c_{\rm p} = c_{\rm V} + R \tag{12}$$

We can write from thermodynamics

$$c_{\rm V} = \left(\frac{\partial U_{\rm m}}{\partial T}\right)_{V} \tag{13}$$

where U_{m} is internal energy per mol $U_{\mathrm{m}} = \mathcal{E}_{\mathrm{m}} \mathcal{N}_{\mathrm{A}}$ and

$$c_{\rm p} = \left(\frac{\partial H_{\rm m}}{\partial T}\right)_{\rm p} \tag{14}$$

where $H_{
m m}$ is enthalpy per mol $H_{
m m}=U_{
m m}+
ho V_{
m m} \Rightarrow$

$$\left(\frac{\partial H_{\rm m}}{\partial T}\right)_{\rho} = \left(\frac{\partial U_{\rm m}}{\partial T}\right)_{\rho} + \rho \left(\frac{\partial V_{\rm m}}{\partial T}\right)_{\rho} \tag{15}$$

giving $c_{\rm p} = c_{\rm V} + R$

Molecular Impingement Flux - Knudsen Equation

The molecular impingement flux at a surface is a fundamental determinant of film deposition rate:

$$\Gamma = n\langle v \cos \theta \rangle = \int_0^\infty \int_0^\pi \int_0^{2\pi} f(v) v^2 \cos \theta \sin \theta d\phi d\theta dv \tag{16}$$

Substituting Maxwell-Boltzmann distribution

$$\Gamma = n \left(\frac{k_{\rm B}T}{2\pi m}\right)^{1/2} = \frac{1}{4} n v_{\rm av} \tag{17}$$

2.5 Units of Measurement

2.6 Knudsen Equation

2.7 Mean Free Path